



4N65K-TC

Power MOSFET

4A, 650V N-CHANNEL POWER MOSFET

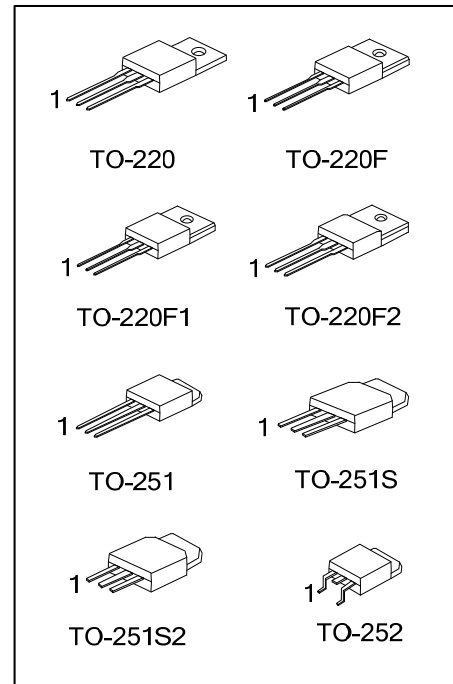
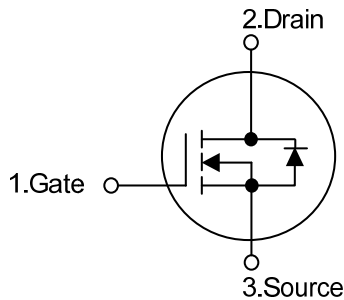
DESCRIPTION

The UTC **4N65K-TC** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristic. This power MOSFET is usually used in high speed switching applications including power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} < 2.5\Omega @ V_{GS} = 10V, I_D = 2.0A$
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

SYMBOL



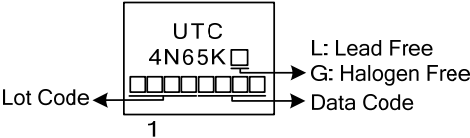
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
4N65KL-TA3-T	4N65KG-TA3-T	TO-220	G	D	S	Tube
4N65KL-TF1-T	4N65KG-TF1-T	TO-220F1	G	D	S	Tube
4N65KL-TF2-T	4N65KG-TF2-T	TO-220F2	G	D	S	Tube
4N65KL-TF3-T	4N65KG-TF3-T	TO-220F	G	D	S	Tube
4N65KL-TM3-T	4N65KG-TM3-T	TO-251	G	D	S	Tube
4N65KL-TMS2-T	4N65KG-TMS2-T	TO-251S2	G	D	S	Tube
4N65KL-TN3-R	4N65KG-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>4N65KG-TA3-T</p>	<p>(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TM3: TO-251, TMS: TO-251S, TMS2: TO-251S2, TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	4.0	A
	Pulsed (Note2)	I_{DM}	16	A
Avalanche Energy	Single Pulsed (Note3)	E_{AS}	113	mJ
Peak Diode Recovery dv/dt (Note4)		dv/dt	3.79	V/ns
Power Dissipation	TO-220	P_D	106	W
	TO-220F/TO-220F1 TO-220F2		36	W
	TO-251/TO-251S TO-251S2/TO-252		50	W
Derate above 25°C	TO-220		0.84	W/ $^\circ\text{C}$
	TO-220F/TO-220F1 TO-220F2		0.29	W/ $^\circ\text{C}$
	TO-251/TO-251S TO-251S2/TO-252		0.40	W/ $^\circ\text{C}$
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature

3. $L=25\text{mH}$, $I_{AS}=3.0\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 4.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction-to-Ambient	TO-220/TO-220F TO-220F1/TO-220F2	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-251/TO-251S TO-251S2/TO-252		83	$^\circ\text{C}/\text{W}$
Junction-to-Case	TO-220	θ_{JC}	1.18	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		3.4	$^\circ\text{C}/\text{W}$
	TO-220F2		3.57	$^\circ\text{C}/\text{W}$
	TO-251/TO-251S TO-251S2/TO-252		2.5	$^\circ\text{C}/\text{W}$

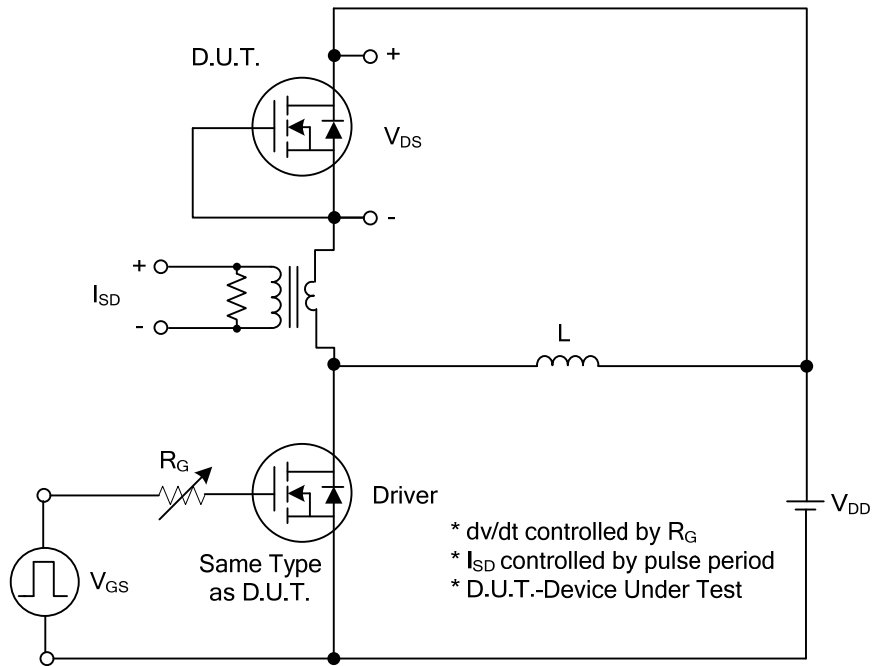
■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = 250μA	650			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}			100	nA
	Reverse				-100	nA
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.6		V/°C
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 2.0A			2.5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} = 25 V, V _{GS} = 0V, f = 1MHz		490		pF
Output Capacitance	C _{OSS}			54		pF
Reverse Transfer Capacitance	C _{RSS}			5.8		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q _G	V _{DS} =50V, V _{GS} =10V, I _D =1.3A I _G = 100μA (Note1, 2)		32		nC
Gate-Source Charge	Q _{GS}			4.2		nC
Gate-Drain Charge	Q _{GD}			5.6		nC
Turn-On Delay Time	t _{D(ON)}	V _{DS} =30V, V _{GS} =10V, I _D =0.5A, R _G =25Ω (Note1, 2)		44		ns
Turn-On Rise Time	t _R			28		ns
Turn-Off Delay Time	t _{D(OFF)}			116		ns
Turn-Off Fall Time	t _F			33		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I _S				4.0	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				16	A
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 4.0A			1.4	V
Reverse Recovery Time	t _{rr}	V _{GS} = 0V, I _S = 4.0A, dI _F / dt =100A/μs (Note 1)		360		nS
Reverse Recovery Charge	Q _{rr}			1.42		μC

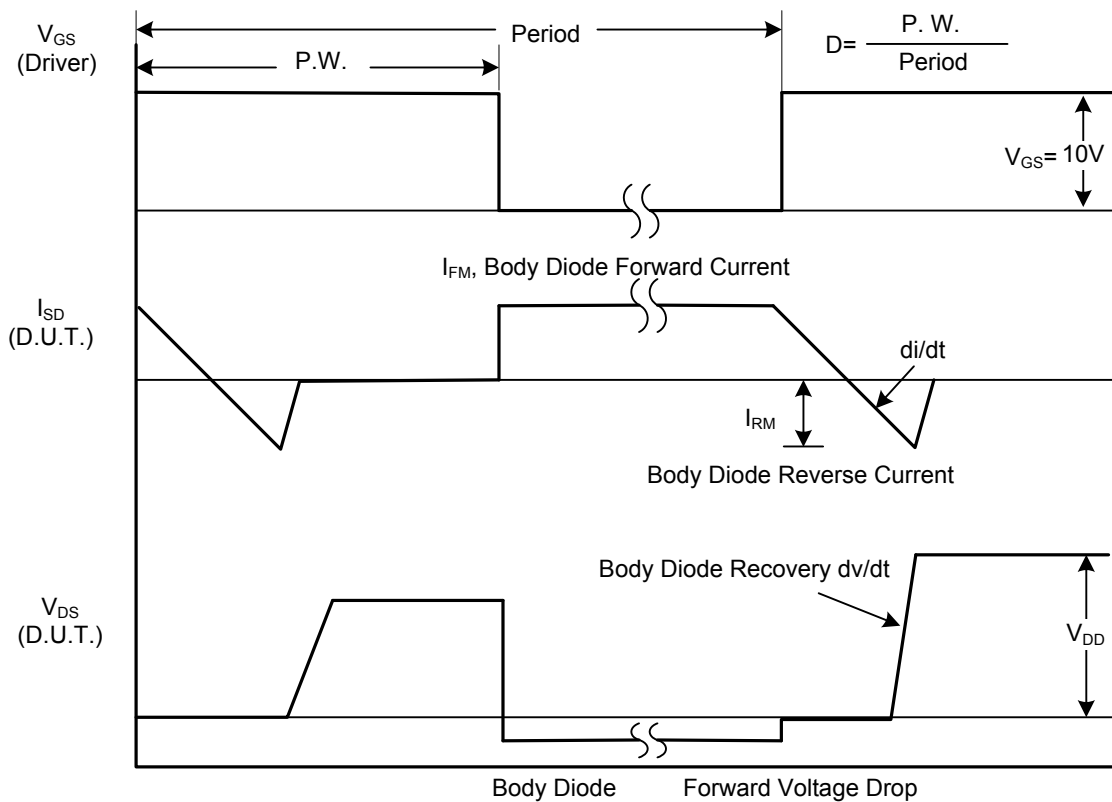
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

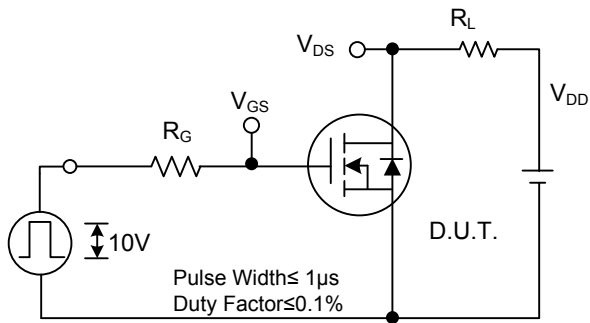


Peak Diode Recovery dv/dt Test Circuit

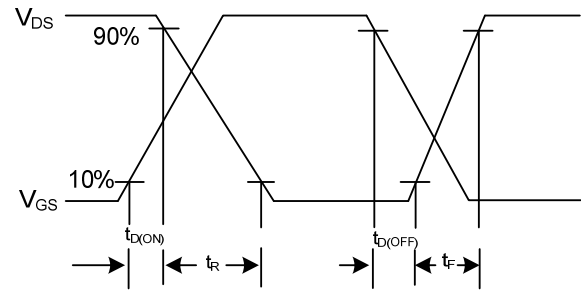


Peak Diode Recovery dv/dt Waveforms

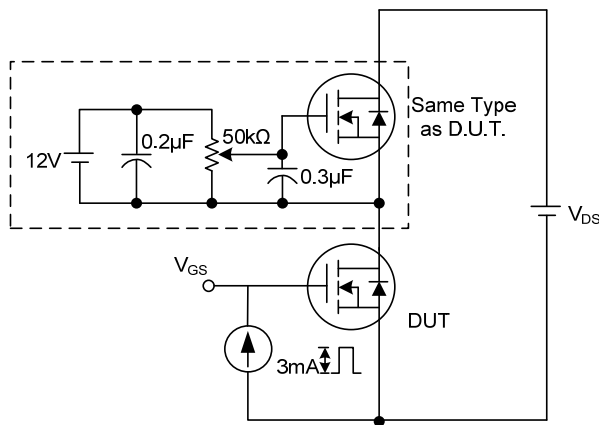
TEST CIRCUITS AND WAVEFORMS (Cont.)



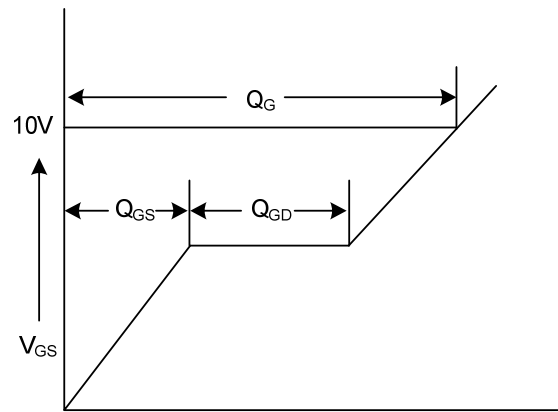
Switching Test Circuit



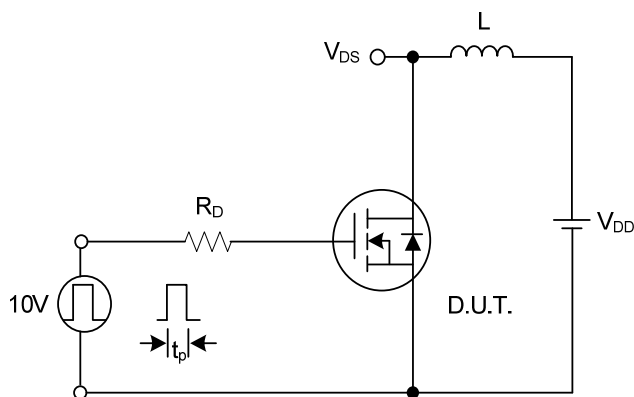
Switching Waveforms



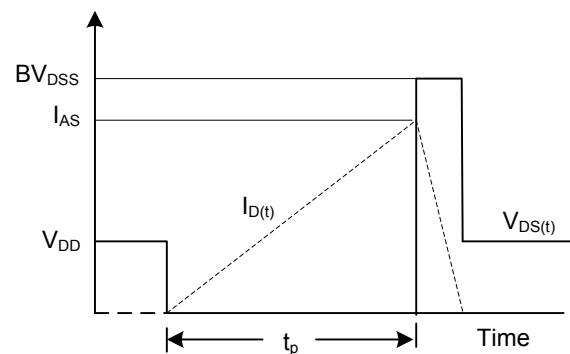
Gate Charge Test Circuit



Gate Charge Waveform

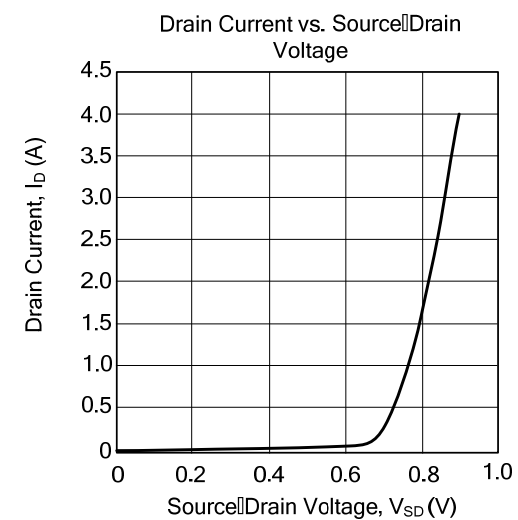
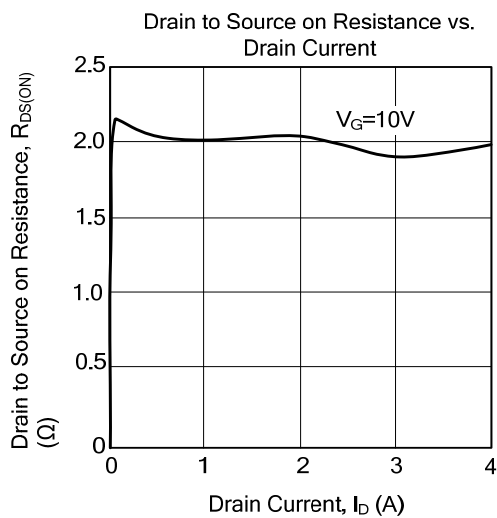
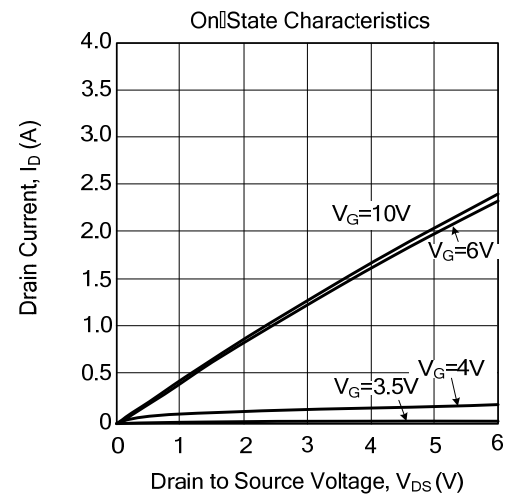
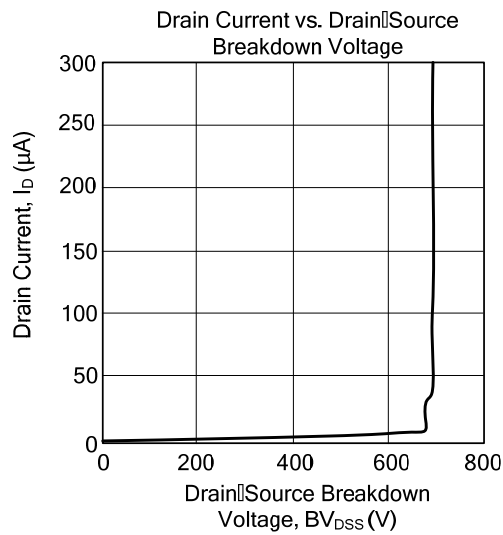
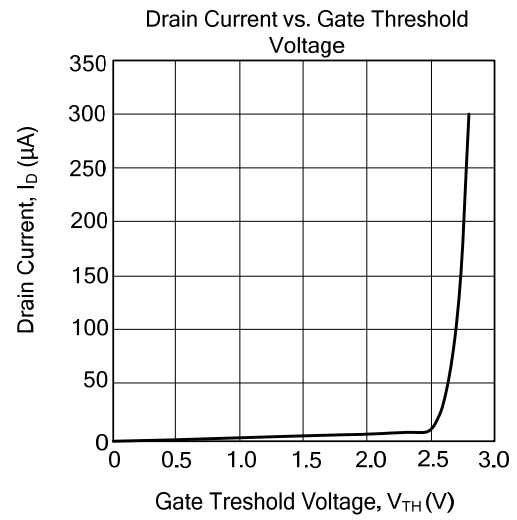
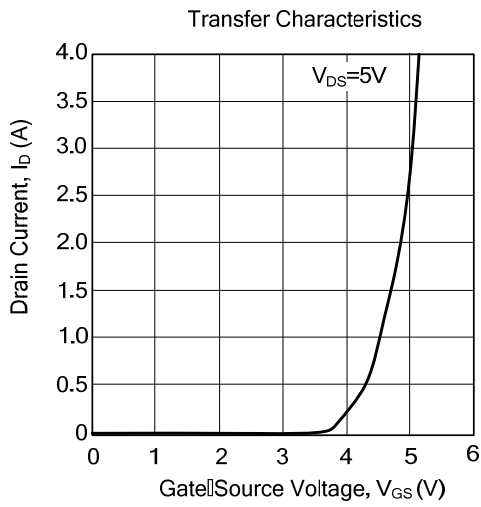


Unclamped Inductive Switching Test Circuit

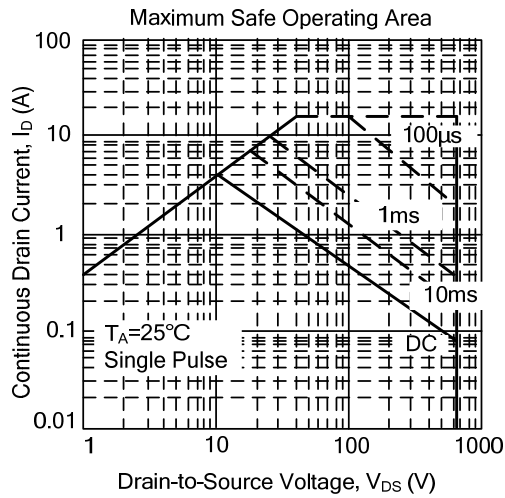


Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



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